1. General description

Planar passivated very sensitive gate Silicon Controlled Rectifier in a TO92 plastic package.

2. Features and benefits

- Planar passivated for voltage ruggedness and reliability
- Very sensitive gate

3. Applications

- Ignition circuits
- Low power latching circuits
- Protection / shut-down circuits: lighting ballasts
- Protection / shut-down circuits: Switched Mode Power Supplies

4. Quick reference data

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Conditions</th>
<th>Conditions</th>
<th>Min</th>
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<th>Max</th>
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<tr>
<td>$V_{RRM}$</td>
<td>repetitive peak reverse voltage</td>
<td>-</td>
<td>-</td>
<td>600</td>
<td>V</td>
<td></td>
<td></td>
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<tr>
<td>$I_{T(AV)}$</td>
<td>average on-state current</td>
<td>half sine wave; $T_{lead} \leq 83 , ^\circ C$; Fig. 1</td>
<td>-</td>
<td>-</td>
<td>0.5</td>
<td>A</td>
<td></td>
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<tr>
<td>$I_{(RMS)}$</td>
<td>RMS on-state current</td>
<td>half sine wave; $T_{lead} \leq 83 , ^\circ C$; Fig. 2; Fig. 3</td>
<td>-</td>
<td>-</td>
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<td>A</td>
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<tr>
<td>$I_{TSM}$</td>
<td>non-repetitive peak on-state current</td>
<td>half sine wave; $T_{j(init)} = 25 , ^\circ C$; $t_p = 10 , ms$; Fig. 4; Fig. 5</td>
<td>-</td>
<td>-</td>
<td>8</td>
<td>A</td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>half sine wave; $T_{j(init)} = 25 , ^\circ C$; $t_p = 8.3 , ms$</td>
<td>-</td>
<td>-</td>
<td>9</td>
<td>A</td>
<td></td>
</tr>
<tr>
<td>$T_j$</td>
<td>junction temperature</td>
<td>-</td>
<td>-</td>
<td>125</td>
<td>°C</td>
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Static characteristics

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<th>Conditions</th>
<th>Min</th>
<th>Typ</th>
<th>Max</th>
<th>Unit</th>
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<tr>
<td>$I_{GT}$</td>
<td>gate trigger current</td>
<td>$V_o = 12 , V$; $I_f = 10 , mA$; $T_j = 25 , ^\circ C$; Fig. 7</td>
<td>15</td>
<td>-</td>
<td>50</td>
<td>μA</td>
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Dynamic characteristics

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<th>Conditions</th>
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<th>Max</th>
<th>Unit</th>
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</thead>
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<tr>
<td>d$V_o$/dt</td>
<td>rate of rise of off-state voltage</td>
<td>$V_{DM} = 402 , V$; $T_j = 125 , ^\circ C$; $R_{OK} = 1 , k\Omega$; $(V_{DM} = 67% , of , V_{DRM})$; exponential waveform; Fig. 12</td>
<td>100</td>
<td>-</td>
<td>-</td>
<td>V/μs</td>
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5. Pinning information

Table 2. Pinning information

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<th>Graphic symbol</th>
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<td>A</td>
<td>anode</td>
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<td></td>
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<tr>
<td>2</td>
<td>G</td>
<td>gate</td>
<td></td>
<td></td>
</tr>
<tr>
<td>3</td>
<td>K</td>
<td>cathode</td>
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6. Ordering information

Table 3. Ordering information

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<th>Package Name</th>
<th>Orderable part number</th>
<th>Packing method</th>
<th>Small packing quantity</th>
<th>Package version</th>
<th>Package issue date</th>
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<td>BT169G-L</td>
<td>TO92</td>
<td>BT169G-L.412</td>
<td>Reel</td>
<td>2000</td>
<td>SOT54 wide pitch</td>
<td>14-Nov-2013</td>
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7. Marking

Table 4. Marking codes

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<td>BT169G-L</td>
<td>BT169GL</td>
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8. Limiting values

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<td>( V_{DRM} )</td>
<td>repetitive peak off-state voltage</td>
<td></td>
<td>-</td>
<td>600</td>
<td>V</td>
</tr>
<tr>
<td>( V_{RRM} )</td>
<td>repetitive peak reverse voltage</td>
<td></td>
<td>-</td>
<td>600</td>
<td>V</td>
</tr>
<tr>
<td>( I_{T(AV)} )</td>
<td>average on-state current</td>
<td>half sine wave; ( T_{j(init)} \leq 83 , ^\circ \text{C} ); \text{Fig. 1}</td>
<td>-</td>
<td>0.5</td>
<td>A</td>
</tr>
<tr>
<td>( I_{T(RMS)} )</td>
<td>RMS on-state current</td>
<td>half sine wave; ( T_{j(init)} \leq 83 , ^\circ \text{C} ); \text{Fig. 2}; \text{Fig. 3}</td>
<td>-</td>
<td>0.8</td>
<td>A</td>
</tr>
<tr>
<td>( I_{TSM} )</td>
<td>non-repetitive peak on-state current</td>
<td>half sine wave; ( T_{j(init)} = 25 , ^\circ \text{C} ); ( t_p = 10 , \text{ms} ); \text{Fig. 4}; \text{Fig. 5}</td>
<td>-</td>
<td>8</td>
<td>A</td>
</tr>
<tr>
<td></td>
<td></td>
<td>half sine wave; ( T_{j(init)} = 25 , ^\circ \text{C} ); ( t_p = 8.3 , \text{ms} )</td>
<td>-</td>
<td>9</td>
<td>A</td>
</tr>
<tr>
<td>( I^2t )</td>
<td>( I^2t ) for fusing</td>
<td>( t_p = 10 , \text{ms} ); \text{SIN}</td>
<td>-</td>
<td>0.32</td>
<td>A,\text{s}</td>
</tr>
<tr>
<td>( dI/dt )</td>
<td>rate of rise of on-state current</td>
<td>( I_T = 2 , \text{A}; , I_Q = 10 , \text{mA}; , dI_Q/dt = 100 , \text{mA/\mu s} )</td>
<td>-</td>
<td>50</td>
<td>A/\mu s</td>
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<td>( I_{GM} )</td>
<td>peak gate current</td>
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<td>-</td>
<td>1</td>
<td>A</td>
</tr>
<tr>
<td>( V_{RGM} )</td>
<td>peak reverse gate voltage</td>
<td></td>
<td>-</td>
<td>5</td>
<td>V</td>
</tr>
<tr>
<td>( P_{GM} )</td>
<td>peak gate power</td>
<td></td>
<td>-</td>
<td>2</td>
<td>W</td>
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<tr>
<td>( P_{G(AV)} )</td>
<td>average gate power</td>
<td>over any 20 ms period</td>
<td>-</td>
<td>0.1</td>
<td>W</td>
</tr>
<tr>
<td>( T_{stg} )</td>
<td>storage temperature</td>
<td></td>
<td>-40</td>
<td>150</td>
<td>°C</td>
</tr>
<tr>
<td>( T_j )</td>
<td>junction temperature</td>
<td>[1]</td>
<td>-</td>
<td>125</td>
<td>°C</td>
</tr>
</tbody>
</table>

[1] Operation above 110°C may require the use of a gate to cathode resistor of 1kΩ or less.

\[ a = \text{form factor} = \frac{I_{T(RMS)}}{I_{T(AV)}} \]
\[ \alpha = \text{conduction angle} \]

**Fig. 1.** Total power dissipation as a function of average on-state current; maximum values
Fig. 2. RMS on-state current as a function of surge duration for sinusoidal currents

\( f = 50 \text{ Hz}; T_{\text{lead}} = 83 \, ^\circ\text{C} \)

Fig. 3. RMS on-state current as a function of lead temperature; maximum values

\( T_{\text{lead}} \) = 83 °C

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal currents cycles; maximum values

\( f = 50 \text{ Hz} \)
Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values
## 9. Thermal characteristics

### Table 6. Thermal characteristics

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Conditions</th>
<th>Min</th>
<th>Typ</th>
<th>Max</th>
<th>Unit</th>
</tr>
</thead>
<tbody>
<tr>
<td>$R_{th(j-lead)}$</td>
<td>thermal resistance from junction to lead</td>
<td>Fig. 6</td>
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<td>-</td>
<td>60</td>
<td>K/W</td>
</tr>
<tr>
<td>$R_{th(j-a)}$</td>
<td>thermal resistance from junction to ambient free air</td>
<td>printed circuit board mounted: lead length = 4 mm</td>
<td>-</td>
<td>150</td>
<td>-</td>
<td>K/W</td>
</tr>
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</table>

![Fig. 6](image-url) Transient thermal impedance from junction to lead as a function of pulse width
## 10. Characteristics

### Table 7. Characteristics

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Parameter</th>
<th>Conditions</th>
<th>Min</th>
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<td>Static characteristics</td>
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<tr>
<td></td>
<td></td>
<td><strong>I&lt;sub&gt;GT&lt;/sub&gt;</strong> gate trigger current</td>
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<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td></td>
<td></td>
<td>$V_D = 12$ V; $I_T = 10$ mA; $T_j = 25$ °C;</td>
<td>15</td>
<td>-</td>
<td>50</td>
<td>μA</td>
</tr>
<tr>
<td></td>
<td></td>
<td><em>Fig. 7</em></td>
<td></td>
<td></td>
<td></td>
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<tr>
<td></td>
<td></td>
<td><strong>I&lt;sub&gt;L&lt;/sub&gt;</strong> latching current</td>
<td></td>
<td>2</td>
<td>4</td>
<td>mA</td>
</tr>
<tr>
<td></td>
<td></td>
<td>$V_D = 12$ V; $I_D = 0.5$ mA; $T_j = 25$ °C;</td>
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<td></td>
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<td><em>Fig. 8</em></td>
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<td></td>
<td><strong>I&lt;sub&gt;H&lt;/sub&gt;</strong> holding current</td>
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<td>1</td>
<td>mA</td>
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<td>$V_D = 12$ V; $T_j = 25$ °C;</td>
<td>-</td>
<td></td>
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<td></td>
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<tr>
<td></td>
<td></td>
<td><em>Fig. 9</em></td>
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<td></td>
<td><strong>V&lt;sub&gt;T&lt;/sub&gt;</strong> on-state voltage</td>
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<td>1.25</td>
<td>1.7</td>
<td>V</td>
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<td>$I_T = 1.2$ A; $T_j = 25$ °C;</td>
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<td><em>Fig. 10</em></td>
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<td>V</td>
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<td><em>Fig. 11</em></td>
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<td>$V_D = 400$ V; $I_T = 10$ mA; $T_j = 125$ °C</td>
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<td>0.3</td>
<td>-</td>
<td>V</td>
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<td></td>
<td><strong>I&lt;sub&gt;0&lt;/sub&gt;</strong> off-state current</td>
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<td>2</td>
<td>μA</td>
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<td>$V_D = 600$ V; $R_{GK} = 1$ kΩ; $T_j = 25$ °C</td>
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<td></td>
<td></td>
<td></td>
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<tr>
<td></td>
<td></td>
<td><strong>I&lt;sub&gt;R&lt;/sub&gt;</strong> reverse current</td>
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<td>-</td>
<td>2</td>
<td>μA</td>
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<td>$V_R = 600$ V; $T_j = 25$ °C; $R_{GK} = 1$ kΩ</td>
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<tr>
<td></td>
<td></td>
<td>$V_R = 600$ V; $T_j = 125$ °C; $R_{GK} = 1$ kΩ</td>
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<td>0.05</td>
<td>0.1</td>
<td>mA</td>
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<td>Dynamic characteristics</td>
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<tr>
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<td><strong>dV&lt;sub&gt;D&lt;/sub&gt;/dt</strong> rate of rise of off-state voltage</td>
<td></td>
<td>100</td>
<td>-</td>
<td>V/μs</td>
</tr>
<tr>
<td></td>
<td></td>
<td>$V_{DM} = 402$ V; $T_j = 125$ °C; $R_{GK} = 1$ kΩ;</td>
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<tr>
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<td></td>
<td>($V_{DM}$ = 67% of $V_{DM}$); exponential waveform; <em>Fig. 12</em></td>
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</table>

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Fig. 7. Normalized gate trigger current as a function of junction temperature

Fig. 8. Normalized latching current as a function of junction temperature

Fig. 9. Normalized holding current as a function of junction temperature

Fig. 10. On-state current as a function of on-state voltage

$T_j = 125 \, ^\circ\text{C}; \text{typical values}$

$T_j = 125 \, ^\circ\text{C}; \text{maximum values}$

$T_j = 25 \, ^\circ\text{C}; \text{maximum values}$
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

(1) $R_{OK} = 1 \, \text{kΩ}$
11. Package outline

**SOT54 PACKAGE OUTLINE**

- **SOT54**
  - Bulk Pack - 412

- **SOT54 LEADS ON CIRCLE**
  - Bulk Pack - 112

- **SOT54 WIDE PITCH**
  - Tape/Reel Pack - 116
  - Ammono Pack - 126

- **SOT54 LEAD BEND L01**
  - Bulk Pack - 412

- **SOT54 LEAD BEND L02**
  - Bulk Pack - 412

Remark: Detailed dimensions refer to POD drawing.
### Symbol Dimensions In Millimeters Dimensions In Inches

<table>
<thead>
<tr>
<th>Symbol</th>
<th>Min</th>
<th>Max</th>
<th>Min</th>
<th>Max</th>
</tr>
</thead>
<tbody>
<tr>
<td>A</td>
<td>3.300</td>
<td>3.700</td>
<td>0.130</td>
<td>0.146</td>
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<tr>
<td>A1</td>
<td>1.100</td>
<td>1.400</td>
<td>0.043</td>
<td>0.055</td>
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<td>b</td>
<td>0.380</td>
<td>0.550</td>
<td>0.015</td>
<td>0.022</td>
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<tr>
<td>c</td>
<td>0.360</td>
<td>0.510</td>
<td>0.014</td>
<td>0.020</td>
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<tr>
<td>D</td>
<td>4.300</td>
<td>4.700</td>
<td>0.169</td>
<td>0.185</td>
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<tr>
<td>E</td>
<td>4.300</td>
<td>4.700</td>
<td>0.169</td>
<td>0.185</td>
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<tr>
<td>e</td>
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<td>0.050</td>
<td>TYP.</td>
</tr>
<tr>
<td>e1</td>
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<td>0.096</td>
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<tr>
<td>L</td>
<td>14.100</td>
<td>14.500</td>
<td>0.555</td>
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12. Legal information

Data sheet status

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<th>Product status</th>
<th>Definition</th>
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<tbody>
<tr>
<td>Objective [short] data sheet</td>
<td>Development</td>
<td>This document contains data from the objective specification for product development.</td>
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<tr>
<td>Preliminary [short] data sheet</td>
<td>Qualification</td>
<td>This document contains data from the preliminary specification.</td>
</tr>
<tr>
<td>Product [short] data sheet</td>
<td>Production</td>
<td>This document contains the product specification.</td>
</tr>
</tbody>
</table>

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.ween-semi.com.

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Date of release: 12 October 2021